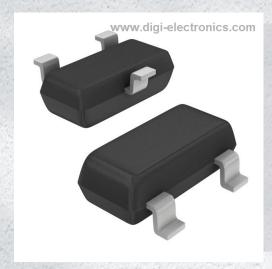


# **MMUN2137LT1G Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number MMUN2137LT1G-DG

Manufacturer onsemi

Manufacturer Product Number MMUN2137LT1G

Description TRANS PREBIAS PNP 50V SOT23-3

Detailed Description Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biase d 50 V 100 mA 246 mW Surface Mount SOT-23-3 (TO

-236)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
MMUN2137LT1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	47 kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
22 kOhms	80 @ 5mA, 10V
Vce Saturation (Max) @ lb, Ic:	Current - Collector Cutoff (Max):
250mV @ 300μA, 10mA	500nA
Power - Max:	Mounting Type:
246 mW	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	SOT-23-3 (TO-236)
Base Product Number:	
MMUN2137	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

## **Digital Transistors (BRT)** $R1 = 47 k\Omega$ , $R2 = 22 k\Omega$

### **PNP Transistors with Monolithic Bias Resistor Network**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

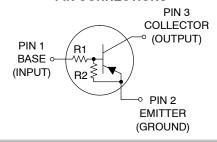
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



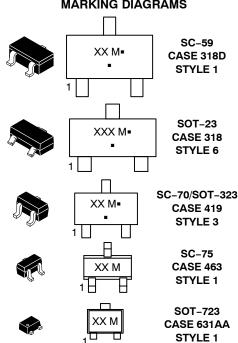
#### ON Semiconductor®

www.onsemi.com

#### **PIN CONNECTIONS**



#### MARKING DIAGRAMS



 Specific Device Code XXX Μ = Date Code\* = Pb-Free Package

IX ME.

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-1123

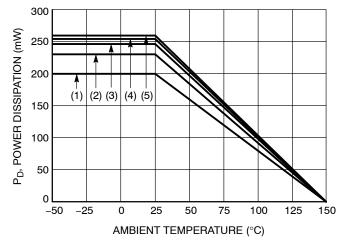
**CASE 524AA** STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2137T1G	6P	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2137LT1G, NSVMMUN2137LT1G*	ACD	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5137T1G	6P	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA144WET1G, NSVDTA144WET1G*	6P	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA144WM3T5G	6P	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA144WF3T5G	D (90°)**	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*\*</sup> $(XX^{\circ})$  = Degree rotation in the clockwise direction.



- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

Figure 1. Derating Curve

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2137)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	230 338 1.8 2.7	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	264 287	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

#### **Table 2. THERMAL CHARACTERISTICS**

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-23) (MMUN2137L)	•		•	
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1)	P <sub>D</sub>	246 400 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 1) (Note 2)	$R_{ heta JA}$	3.2 508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ heta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5137)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	280 332	°C/W
Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTA144WE)				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	600 400	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTA144WM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{\thetaJA}$	480 205	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-1123) (NSBA144WF3)				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 3) (Note 4) (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ hetaJL}$	193	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- FR-4 @ Minimum Pad.
   FR-4 @ 1.0 x 1.0 Inch Pad.
   FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_{E} = 0)$	I <sub>CBO</sub>	_	_	100	nAdc	
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	_	500	nAdc	
Emitter–Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_{C} = 0)$	I <sub>EBO</sub>	-	-	0.13	mAdc	
Collector–Base Breakdown Voltage ( $I_C = 10 \ \mu\text{A}, \ I_E = 0$ )	V <sub>(BR)</sub> CBO	50	_	-	Vdc	
Collector-Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	-	Vdc	
ON CHARACTERISTICS						
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	140	-		
Collector – Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	VCE(sat)	_	_	0.25	Vdc	
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	-	1.8	1.2	Vdc	
Input Voltage (on) ( $V_{CE} = 0.3 \text{ V}, I_{C} = 2.0 \text{ mA}$ )	V <sub>i(on)</sub>	4.0	2.4	-	Vdc	
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 4.0 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc	
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc	
Input Resistor	R1	32.9	47	61.1	kΩ	
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	1.7	2.1	2.6		

<sup>5.</sup> Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq$  2%.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## TYPICAL CHARACTERISTICS MUN2137, MMUN2137L, MUN5137, DTA144WE, DTA144WM3

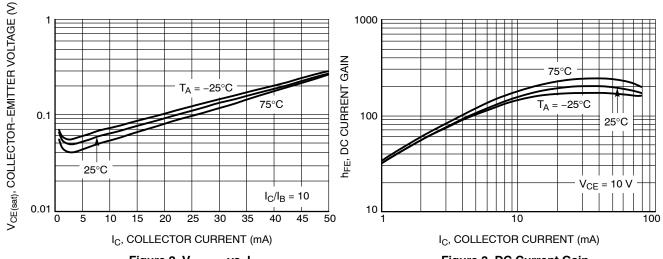


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

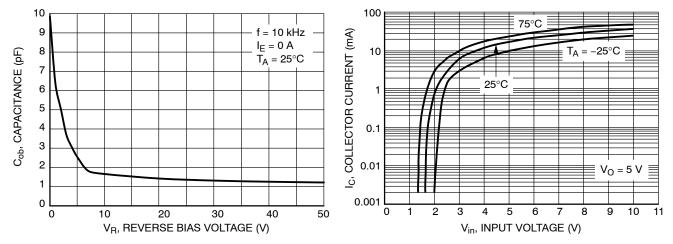


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

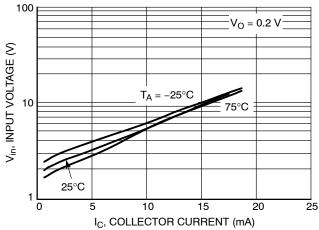


Figure 6. Input Voltage vs. Output Current

#### TYPICAL CHARACTERISTICS NSBA144WF3

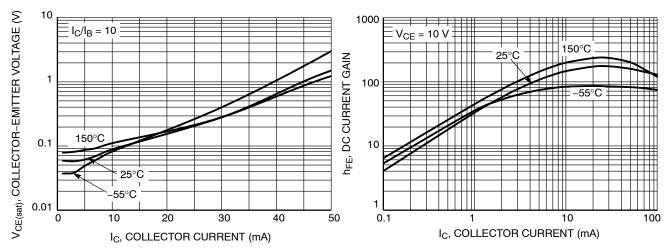
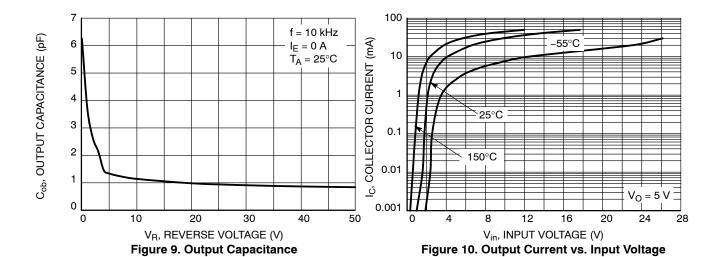


Figure 7. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 8. DC Current Gain



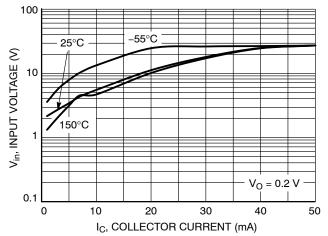


Figure 11. Input Voltage vs. Output Current

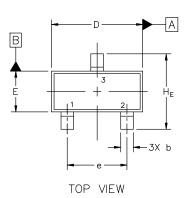


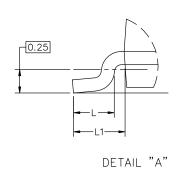
### PACKAGE DIMENSIONS



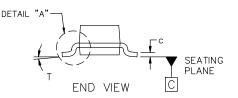
#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 





SIDE VIEW



MILLIMETERS					
DIM	MIN	NOM	MAX		
А	0.89	1.00	1.11		
A1	0.01	0.06	0.10		
b	0.37	0.44	0.50		
С	0.08	0.14	0.20		
D	2.80	2.90	3.04		
E	1.20	1.30	1.40		
е	1.78	1.90	2.04		
L	0.30	0.43	0.55		
L1	0.35	0.54	0.69		
HE	2.10	2.40	2.64		
Т	0°		10°		

#### NOTES:

- DIMENSIONING AND TOLERANCING 1.
- PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

#### **GENERIC MARKING DIAGRAM\***

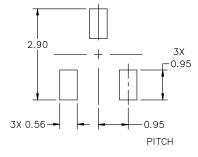


XXX = Specific Device Code

= Date Code

= Pb-Free Package

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.



Scale 3:1

#### RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"		
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P		PAGE 1 OF 2	

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#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7:         STYLE 8:           PIN 1. EMITTER         PIN 1. ANOD           2. BASE         2. NO CC           3. COLLECTOR         3. CATHO	ONNECTION	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11:         STYLE 12:           PIN 1.         ANODE         PIN 1.         CATHO           2.         CATHODE         2.         CATHO           3.         CATHODE-ANODE         3.         ANODO	ODE 2. DRAIN 2. GATE	
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17:         STYLE 18:           PIN 1. NO CONNECTION         PIN 1. NO CO           2. ANODE         2. CATHO           3. CATHODE         3. ANODO	ODE 2. ANODE 2. ANODE	
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23:         STYLE 24:           PIN 1. ANODE         PIN 1. GATE           2. ANODE         2. DRAIN           3. CATHODE         3. SOURCE		CTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Reportant Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P			

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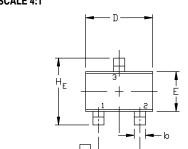


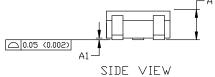
PACKAGE DIMENSIONS



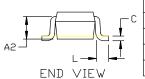
**DATE 11 OCT 2022** 







TOP VIEW



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M)	LLIMETE	RS		INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC		0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



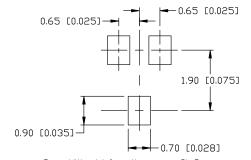


XX = Specific Device Code

= Date Code М

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER 2. BASE	STYLE 7: PIN 1. BASE 2. EMITTER	STYLE 8: PIN 1. GATE 2. SOURCE	STYLE 9: PIN 1. ANODE 2. CATHODE	STYLE 10: PIN 1. CATHODE 2. ANODE	STYLE 11: PIN 1. CATHODE 2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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PACKAGE DIMENSIONS

#### SC75-3 1.60x0.80x0.80, 1.00P

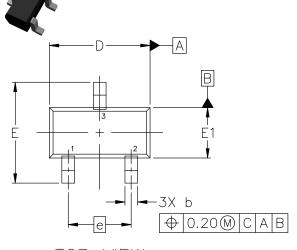
**CASE 463 ISSUE H** 

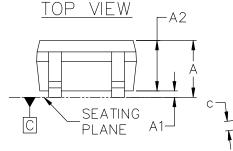
**DATE 01 FEB 2024** 

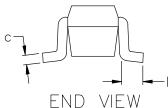
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

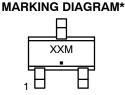
DIM	MILLIMETERS			
DIIVI	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	(	0.80 REF.		
Ь	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
E	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	







## SIDE VIEW **GENERIC**



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	
PIN 1. BASE	
2. EMITTER	

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3 CATHODE RECOMMENDED MOUNTING FOOTPRINT\*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

	SC75_3 1 60x0 80x0 80 1 (		PAGE 1 OF 1	
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## **PACKAGE DIMENSIONS**



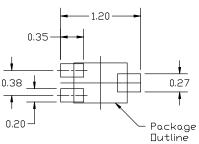
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. 1.
- CONTROLLING DIMENSION: MILLIMETERS. 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

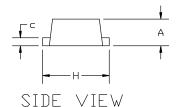
MILLIMETERS				
DIM	MIN	NDM	MAX	
Α	0.34	0.37	0.40	
b	0.15	0.22	0.28	
b1	0.10	0.15	0.20	
<b>C</b>	0.07	0.12	0.17	
D	0.75	0.80	0.85	
Е	0.55	0.60	0.65	
е	0.35	0.38	0.40	
Н	0.950	1.000	1.050	
L	0.185 REF			
L2	0.05 0.10 0.15			

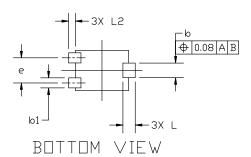


### RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

TOP VIEW





#### **GENERIC MARKING DIAGRAM\***



= Specific Device Code

= Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1

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PACKAGE DIMENSIONS

MILLIMETERS

 $N\square M$ .

0.50

0.21

0.31

0.12

1.20

0.80

0.40 BSC

1.20

0.29 REF



#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

MAX.

0.55

0.27

0.37

0.17

1.25

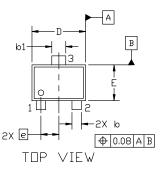
0.85

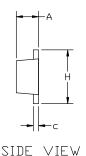
1.25

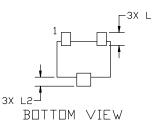
0.25

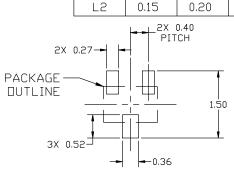
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

b

b1

 $\subset$ D

Ε

е Н

L

MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

#### RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
<ol><li>EMITTER</li></ol>	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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